

60V DUAL PNP SMALL SIGNAL TRANSISTOR IN SOT-563

Description

This bipolar junction transistor (BJT) is designed to meet the stringent requirement of automotive applications.

Features

- BV_{ceo} > -60V
- I_C = -600mA Collector Current
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The MMDT2907VQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: SOT-563
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.003 grams (Approximate)

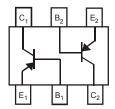
SOT-563





Top View

Bottom View



Device Schematic

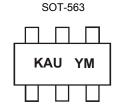
Ordering Information (Note 4)

Ī	Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
	MMDT2907VQ-7	Automotive	KAU	7	8mm	3000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



KAU = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	Н	I	J	K	L	М	N	0	Р	R	S	Т
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	Ic	-600	mA

Thermal Characteristics

Total Power Dissipation (Note 5)	P _D	150	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ heta JA}$	833	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

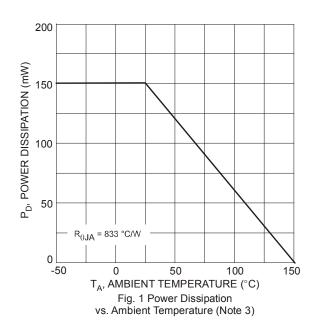
ESD Ratings (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 5

6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information



^{5.} For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.



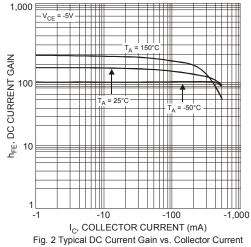
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

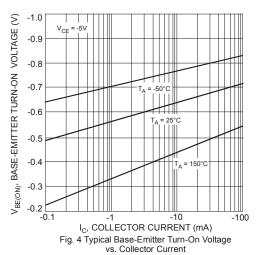
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	BV _{CBO}	-60	_	V	$I_C = -10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 7)	BV _{CEO}	-60	_	V	$I_C = -10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	-5	_	V	$I_E = -10\mu A, I_C = 0$
Collector Cut-Off Current	I _{CBO}		-10	nA	$V_{CB} = -50V, I_E = 0$
	ICBO			μΑ	$V_{CB} = -50V, I_E = 0, T_A = +125^{\circ}C$
Collector Cut-Off Current	ICEX	_	-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -0.5V$
Base Cut-Off Current	I_{BL}		-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -0.5V$
ON CHARACTERISTICS			•		
		75	_		$I_C = -100\mu A, V_{CE} = -10V$
		100	_		$I_C = -1.0 \text{mA}, V_{CE} = -10 \text{V}$
DC Current Gain (Note 7)	h _{FE}	100		_	$I_C = -10 \text{mA}, V_{CE} = -10 \text{V}$
		100	300		$I_C = -150 \text{mA}, V_{CE} = -10 \text{V}$
		50	_		$I_C = -500 \text{mA}, V_{CE} = -10 \text{V}$
Collector-Emitter Saturation Voltage (Note 7)	V _{CE(sat)}		-0.4	V	$I_C = -150 \text{mA}, I_B = -15 \text{mA}$
Obligation Entitles Outditation Vallage (Note 1)	V CE(sat)		-1.6		$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Base-Emitter Saturation Voltage (Note 7)	V _{BE(sat)}	_	-1.3 -2.6	V	$I_C = -150 \text{mA}, I_B = -15 \text{mA}$
5 \ ,	V BE(sat)				$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
SMALL SIGNAL CHARACTERISTICS			•		
Output Capacitance	C _{obo}		8.0	pF	$V_{CB} = -10V$, $f = 1MHz$, $I_E = 0$
Input Capacitance	C _{ibo}		30	pF	$V_{EB} = -2V$, $f = 1MHz$, $I_{C} = 0$
Current Gain-Bandwidth Product	f⊤	200	_	MHz	$V_{CE} = -20V, I_{C} = -50mA,$ f = 100MHz
SWITCHING CHARACTERISTICS			•		
Turn-On Time	t _{off}	_	45	ns	V 00V I 450A
Delay Time	t _d	_	10	ns	$V_{CC} = -30V, I_{C} = -150mA,$
Rise Time	t _r	_	40	ns	I _{B1} = -15mA
Turn-Off Time	t _{off}		100	ns	\/ - C\/ - 450mA
Storage Time	ts	_	80	ns	$V_{CC} = -6V, I_C = -150mA,$
Fall Time	t _f		30	ns	$I_{B1} = I_{B2} = -15mA$

Note: 7. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)





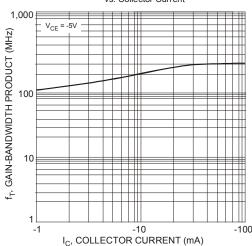


Fig. 6 Typical Gain-Bandwidth Product vs. Collector Current

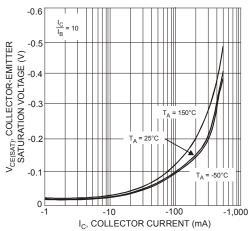
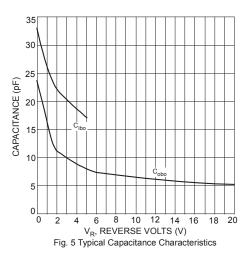


Fig. 3 Typical Collector-Emitter Saturation Voltage vs. Collector Current



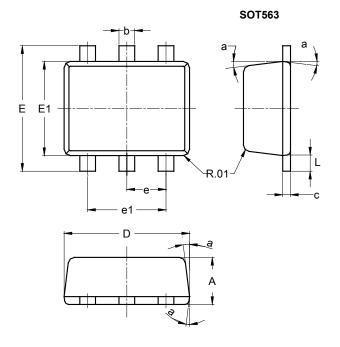
-1.6 V_{CE}, COLLECTOR-EMITTER VOLTAGE (V) -1.2 -1.0 -0.8 -0.6 -0.4 -0.2 0 -0.001 -0.01 -0.1 -100 I_B, BASE CURRENT (mA)

Fig. 7 Typical Collector Saturation Region



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

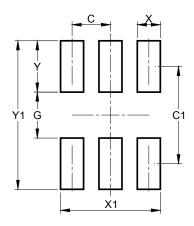


SOT563						
Dim	Min	Max	Тур			
Α	0.55	0.60	0.60			
b	0.15	0.30	0.20			
С	0.10	0.18	0.11			
D	1.50	1.70	1.60			
Е	1.55	1.70	1.60			
E1	1.10	1.25	1.20			
е			0.50			
e1	0.90	1.10	1.00			
L	0.10	0.30	0.20			
а	8°	9°	7°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT563



Dimensions	Value (in mm)
С	0.500
C1	1.270
G	0.600
Х	0.300
X1	1.300
Υ	0.670
Y1	1 940



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